



SHEET 1 OF 1

INFORMATION DISCLOSURE
CITATION IN AN
APPLICATION

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Tetsuzo UEDA, et al.FILING DATE
March 30, 2004GROUP
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U.S. PATENT DOCUMENTS

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FOREIGN PATENT DOCUMENTS

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EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	
SWL		ONOJIMA, Norio., et al. "Growth of AlN (1120) on 6HSiC (1120) by Molecular Epitaxy." Jpn J. Appl. Phys. Vol. 41 (2002) pp. L 1348-1350	
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